

CentralTM Semiconductor Corp.

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Manufacturers of World Class Discrete Semiconductors

1N457A
1N459A

SILICON DIODE

JEDEC DO-35 CASE

DESCRIPTION

The CENTRAL SEMICONDUCTOR 1N457A, 1N459A types are silicon planar diodes designed for low leakage applications.

MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$)

	<u>SYMBOL</u>	<u>1N457A</u>	<u>1N459A</u>	<u>UNITS</u>
Peak Repetitive Reverse Voltage	V_{RRM}	70	200	V
Peak Working Reverse Voltage	V_{RWM}	60	175	V
Average Forward Current	I_O	200	200	mA
Forward Steady-State Current	I_F	500	500	mA
Peak Forward Surge Current (1.0us pulse)	I_{FSM}	4.0	4.0	A
Power Dissipation	P_D	500	500	mW
Operating and Storage Junction Temperature	T_J, T_{stg}	-65 to +200		$^\circ\text{C}$

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted)

<u>SYMBOL</u>	<u>TEST CONDITIONS</u>	<u>1N457A</u>		<u>1N459A</u>		<u>UNITS</u>
		<u>MIN</u>	<u>MAX</u>	<u>MIN</u>	<u>MAX</u>	
BV_R	$I_R = 100\mu\text{A}$	70		200		V
I_R	$V_R = \text{Rated } V_{RWM}$		25		25	nA
I_R	$V_R = \text{Rated } V_{RWM}, T_A = 150^\circ\text{C}$		5.0		5.0	μA
V_F	$I_F = 100\text{mA}$		1.0		1.0	V
C_T	$V_r = 0, f = 1\text{MHz}$		6.0		6.0	pF